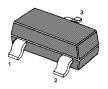
MMBT28S

NPN Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into one group, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



Base 2. Emitter 3. Collector
 TO-236 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	Ic	1	А
Peak Collector Current	I _{CM}	1.25	А
Base Current	l _Β	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	-55 to +150	°C











Dated: 16/03/2015 Rev:01

Characteristics at T_a =25 °C

	B 41		
Symbol	Min.	Max.	Unit
h _{FE}	45	-	-
h _{FE}	200	1000	-
h _{FE}	40	-	-
$V_{(BR)CBO}$	40	-	V
$V_{(BR)CEO}$	20	-	V
$V_{(BR)EBO}$	6	-	V
I _{CBO}	-	100	nA
I _{EBO}	-	100	nA
$V_{CE(sat)}$	-	0.55	V
$V_{BE(sat)}$	-	1.2	V
V_{BE}	-	1.0	V
f _T	100	-	MHz
C _{OB}	-	9	pF
	h _{FE} h _{FE} V _{(BR)CBO} V _{(BR)CEO} V _{(BR)EBO} I _{CBO} I _{EBO} V _{CE(sat)} V _{BE} f _T	h _{FE} 45 h _{FE} 200 h _{FE} 40 V _{(BR)CBO} 40 V _{(BR)CBO} 20 V _{(BR)EBO} 6 I _{CBO} - I _{EBO} - V _{CE(sat)} - V _{BE} - f _T 100	hFE 45 - hFE 200 1000 hFE 40 - V(BR)CBO 40 - V(BR)CBO 20 - V(BR)EBO 6 - ICBO - 100 VCE(sat) - 0.55 VBE(sat) - 1.2 VBE - 1.0 fT 100 -









